NSN 5961-01-051-8624

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Thyristor Semiconductor Device - Page 1 of 1



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View Online at https://aerobasegroup.com/nsn/5961-01-051-8624	
Inclosure Material:	
Metal	
Overall Length:	
Between 1.470 inches and 1.645 inches	
Mounting Facility Quantity:	
1	
Mounting Method:	
Threaded stud	
Overall Width Across Flats:	
Between 0.540 inches and 0.570 inches	
Thread Size:	
0.250 inches	
Semiconductor Material:	
Silicon	
Voltage Rating In Volts Per Characteristic:	
800.0 repetitive peak reverse voltage and 10.0 peak gate voltage	
Current Rating Per Characteristic:	
6.00 amperes forward current, total rms of standard range and 35.00 amperes forward current, total rms horsepower metric	
Power Rating Per Characteristic:	
2.0 watts small-signal input power, common-collector blank	
Maximum Operating Tempurature Per Measurement Point:	
125.0 degrees celsius junction	
Test Data Document:	
72914-55-0830 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing,	awing, etc
excludes any specification, standard or other document that may be referenced in a basic governing drawing)	
Thread Series Designator:	
Unf	
Terminal Type And Quantity:	
2 tab, solder lug and 1 threaded stud	
Shelf Life:	
N/a	
Unit Of Measure:	
Demilitarization:	
No	
Fiig:	